# Small Signal MOSFET

-20 V, -200 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

#### Features

- Dual P-Channel MOSFET
- Offers a Low R<sub>DS(on)</sub> Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb–Free Device

#### Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T = 25°C unless otherwise specified)

| Parameter   |   | Symbol              | Value            | Unit |    |  |
|---|---|---------------------|------------------|------|----|--|
| Drain-to-Source Voltage   |   |                     | V <sub>DSS</sub> | -20  | V  |  |
| Gate-to-Source Voltag   | е                                       |                     | V <sub>GS</sub>  | ±8   | V  |  |
| Continuous Drain  | Steady                                  | $T_A = 25^{\circ}C$ |                  | -200 |    |  |
| Current (Note 1)  | State                                   | $T_A = 85^{\circ}C$ | I <sub>D</sub>   | -140 | mA |  |
|   | t ≤ 5 s                                 | $T_A = 25^{\circ}C$ |                  | -250 |    |  |
| Power Dissipation   | Steady                                  |                     |                  | -125 |    |  |
| (Note 1)  | State                                   | $T_A = 25^{\circ}C$ | PD               |      | mW |  |
|   | t ≤ 5 s                                 |                     |                  | -200 |    |  |
| Pulsed Drain Current  | Pulsed Drain Current $t_p = 10 \ \mu s$ |                     |                  | -600 | mA |  |
| Operating Junction and Storage Temperature                        |   | TJ,<br>T            | -55 to           | °C   |    |  |
|   |   |                     | T <sub>STG</sub> | 150  |    |  |
| Source Current (Body Diode) (Note 2)                              |   |                     | I <sub>S</sub>   | -200 | mA |  |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) |   |                     | ΤL               | 260  | °C |  |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. Surface-mounted on FR4 board using the minimum recommended pad size,

1 oz Cu.

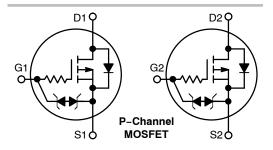
2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

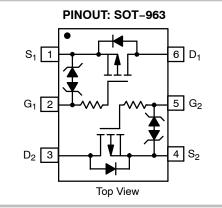


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#### http://onsemi.com

| V <sub>(BR)DSS</sub> | V <sub>(BR)DSS</sub> R <sub>DS(ON)</sub> MAX |        |
|----------------------|--|--------|
| –20 V                | 5.0 Ω @ –4.5 V                               |        |
|                      | 6.0 Ω @ –2.5 V                               | -0.2 A |
|                      | 7.0 Ω @ –1.8 V                               | -0.2 A |
|                      | 10 Ω @ –1.5 V                                |        |









= Date Code

4

М

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= Pb-Free Package

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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#### THERMAL RESISTANCE RATINGS

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| Parameter                                   | Symbol        | Мах  | Unit |
|---|---------------|------|------|
| Junction-to-Ambient - Steady State (Note 3) | $R_{	hetaJA}$ | 1000 | °C/W |
| Junction-to-Ambient – t = 5 s (Note 3)      |               | 600  |      |

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

| Parameter                             | Symbol               | Test Condition  |   | Min  | Тур  | Max  | Unit |
|---------------------------------------|----------------------|---|---|------|------|--|------|
| OFF CHARACTERISTICS                   |                      |   |   |      |      | <u>.                                    </u> |      |
| Drain-to-Source Breakdown Voltage     | V <sub>(BR)DSS</sub> | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \ \mu\text{A}$                        |   | -20  |      |  | V    |
| Zero Gate Voltage Drain Current       | I <sub>DSS</sub>     | $V_{GS}$ = 0 V, $V_{DS}$ = -5.0 V   | $V_{GS} = 0 V, V_{DS} = -5.0 V$ $T_{J} = 25^{\circ}C$ |      |      | -50  |      |
|                                       |                      | $V_{GS}$ = 0 V, $V_{DS}$ = -5.0 V   | T <sub>J</sub> = 85°C                                 |      |      | -100   | nA   |
|                                       |                      | $V_{GS} = 0 V, V_{DS} = -16 V$  | $T_J = 25^{\circ}C$                                   |      |      | -200   |      |
| Gate-to-Source Leakage Current        | I <sub>GSS</sub>     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = :  | ±5.0 V  |      |      | ±100   | nA   |
| ON CHARACTERISTICS (Note 4)           |                      |   |   |      |      |  |      |
| Gate Threshold Voltage                | V <sub>GS(TH)</sub>  | $V_{GS} = V_{DS}$ , $I_D = -250 \ \mu A$  |   | -0.4 |      | -1.0   | V    |
| Drain-to-Source On Resistance         | R <sub>DS(ON)</sub>  | $V_{GS} = -4.5 \text{ V}, \text{ I}_{\text{D}} = -100 \text{ mA}$                 |   |      | 2.0  | 5.0  | Ω    |
|                                       |                      | $V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -50 \text{ mA}$                         |   |      | 2.6  | 6.0  |      |
|                                       |                      | $V_{GS} = -1.8 \text{ V}, \text{ I}_{D} = -20 \text{ mA}$                         |   |      | 3.4  | 7.0  |      |
|                                       |                      | $V_{GS} = -1.5 \text{ V}, \text{ I}_{D} = -10 \text{ mA}$                         |   |      | 4.0  | 10   |      |
|                                       |                      | $V_{GS} = -1.2 \text{ V}, \text{ I}_D = -1.0 \text{ mA}$                          |   |      | 6.0  |  |      |
| Forward Transconductance              | 9 <sub>FS</sub>      | $V_{DS} = -5.0 \text{ V}, \text{ I}_{D} = -125 \text{ mA}$                        |   |      | 0.35 |  | S    |
| Source-Drain Diode Voltage            | V <sub>SD</sub>      | $V_{GS} = 0 \text{ V}, \text{ I}_{S} = -10 \text{ mA}$                            |   |      | -0.6 | -1.0   | V    |
| CHARGES, CAPACITANCES AND GATE        | RESISTANCE           |   |   |      |      |  |      |
| Input Capacitance                     | C <sub>ISS</sub>     | f = 1 MHz, V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = -15 V                       |   |      | 13.5 |  |      |
| Output Capacitance                    | C <sub>OSS</sub>     |   |   |      | 3.8  |  | pF   |
| Reverse Transfer Capacitance          | C <sub>RSS</sub>     |   |   |      | 2.0  |  |      |
| SWITCHING CHARACTERISTICS, $V_{GS}$ = | 4.5 V (Note 4)       | -   |   | -    | -    | - <b>-</b>                                   |      |
| Turn-On Delay Time                    | t <sub>d(ON)</sub>   | $V_{GS}$ = -4.5 V, $V_{DD}$ = -15 V,<br>$I_{D}$ = -200 mA, $R_{G}$ = 2.0 $\Omega$ |   |      | 26   |  | ns   |
| Rise Time                             | t <sub>r</sub>       |   |   |      | 46   |  |      |
| Turn-Off Delay Time                   | t <sub>d(OFF)</sub>  |   |   |      | 196  |  |      |
| Fall Time                             | t <sub>f</sub>       |   |   |      | 145  |  |      |

4. Switching characteristics are independent of operating junction temperatures

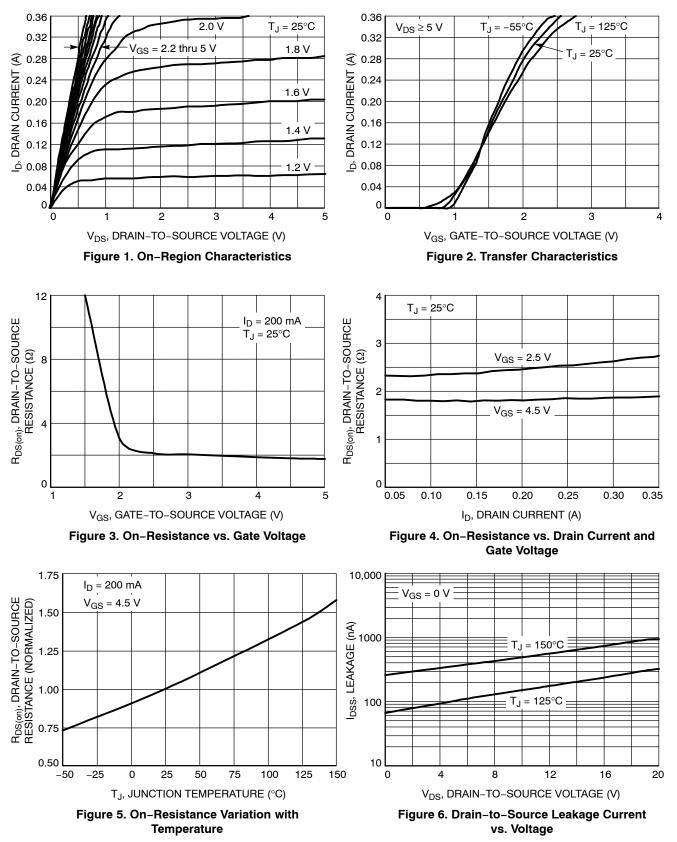
#### **ORDERING INFORMATION**

| Device        | Package              | Shipping <sup>†</sup> |
|---------------|----------------------|-----------------------|
| NTUD3171PZT5G | SOT-963<br>(Pb-Free) | 8000 / Tape & Reel    |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **TYPICAL CHARACTERISTICS**

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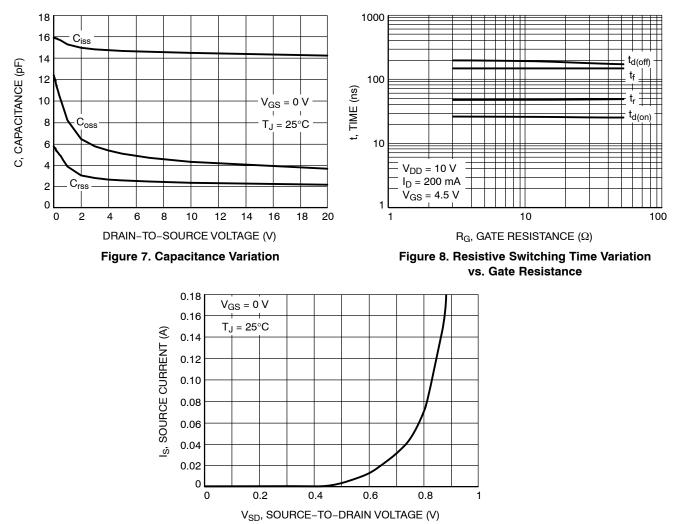
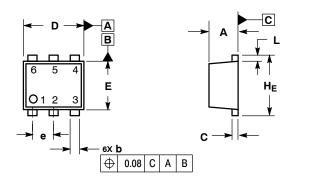


Figure 9. Diode Forward Voltage vs. Current

#### PACKAGE DIMENSIONS

SOT-963 CASE 527AD-01 ISSUE D



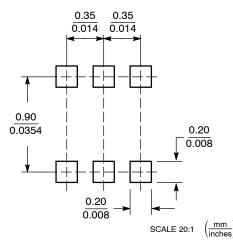
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 3.

TI4-300, 1962. CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

|     | MILLIMETERS |      |      | INCHES |          |       |
|-----|-------------|------|------|--------|----------|-------|
| DIM | MIN         | NOM  | MAX  | MIN    | NOM      | MAX   |
| Α   | 0.34        | 0.37 | 0.40 |        |          |       |
| b   | 0.10        | 0.15 | 0.20 | 0.004  | 0.006    | 0.008 |
| С   | 0.07        | 0.12 | 0.17 | 0.003  | 0.005    | 0.007 |
| D   | 0.95        | 1.00 | 1.05 | 0.037  | 0.039    | 0.041 |
| Е   | 0.75        | 0.80 | 0.85 | 0.03   | 0.032    | 0.034 |
| e   | 0.35 BSC    |      |      | (      | ).014 BS | C     |
| L   | 0.05        | 0.10 | 0.15 | 0.002  | 0.004    | 0.006 |
| ΗE  | 0.95        | 1.00 | 1.05 | 0.037  | 0.039    | 0.041 |

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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